

/ Descriptions

TO-262 N MOS N-CHANNEL MOSFET in a TO-262 Plastic Package..

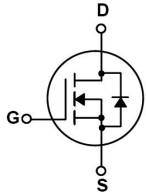
/ Features

Low gate charge, low crss, fast switching.

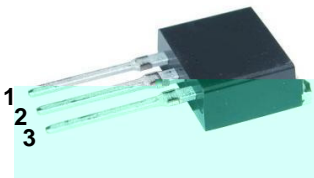
/ Applications

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

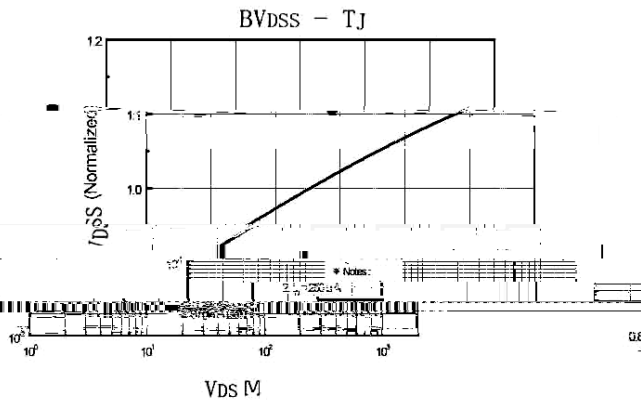
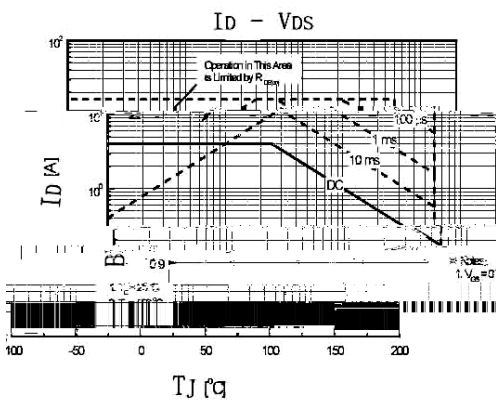
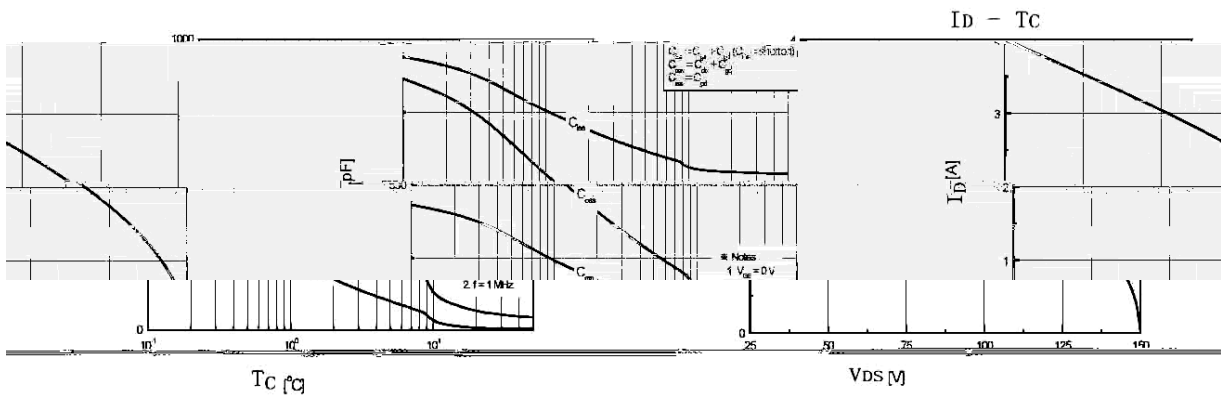
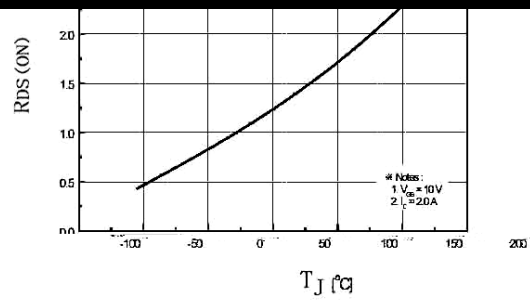
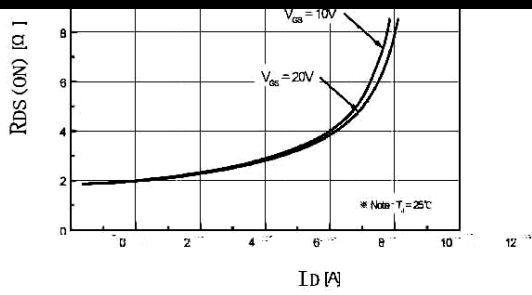
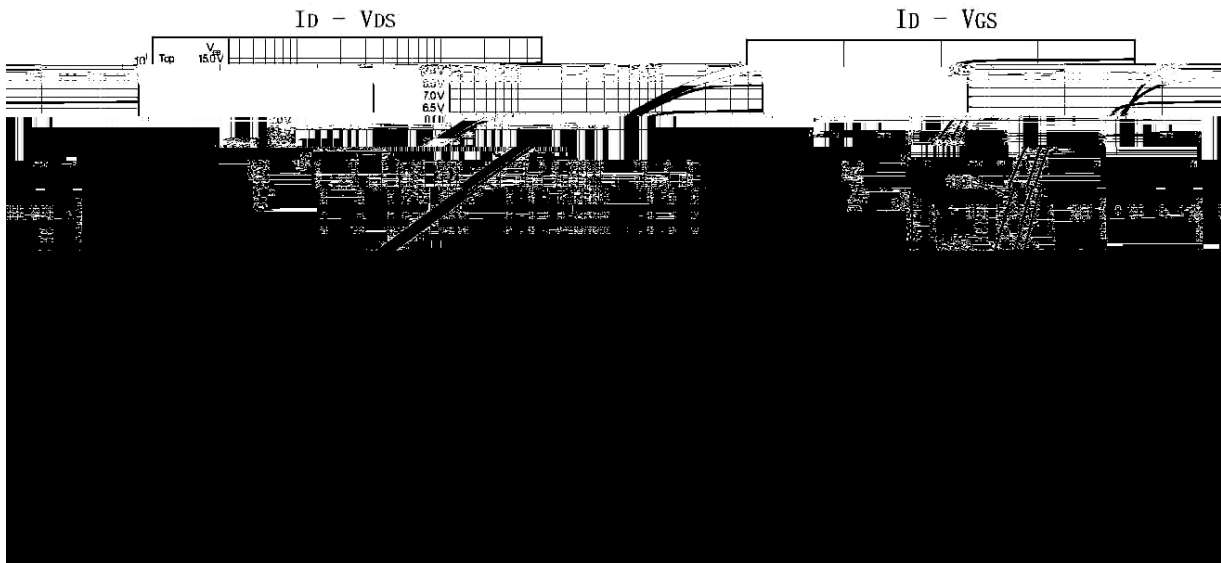
/ h_{FE} Classifications & Marking

See Marking Instructions.

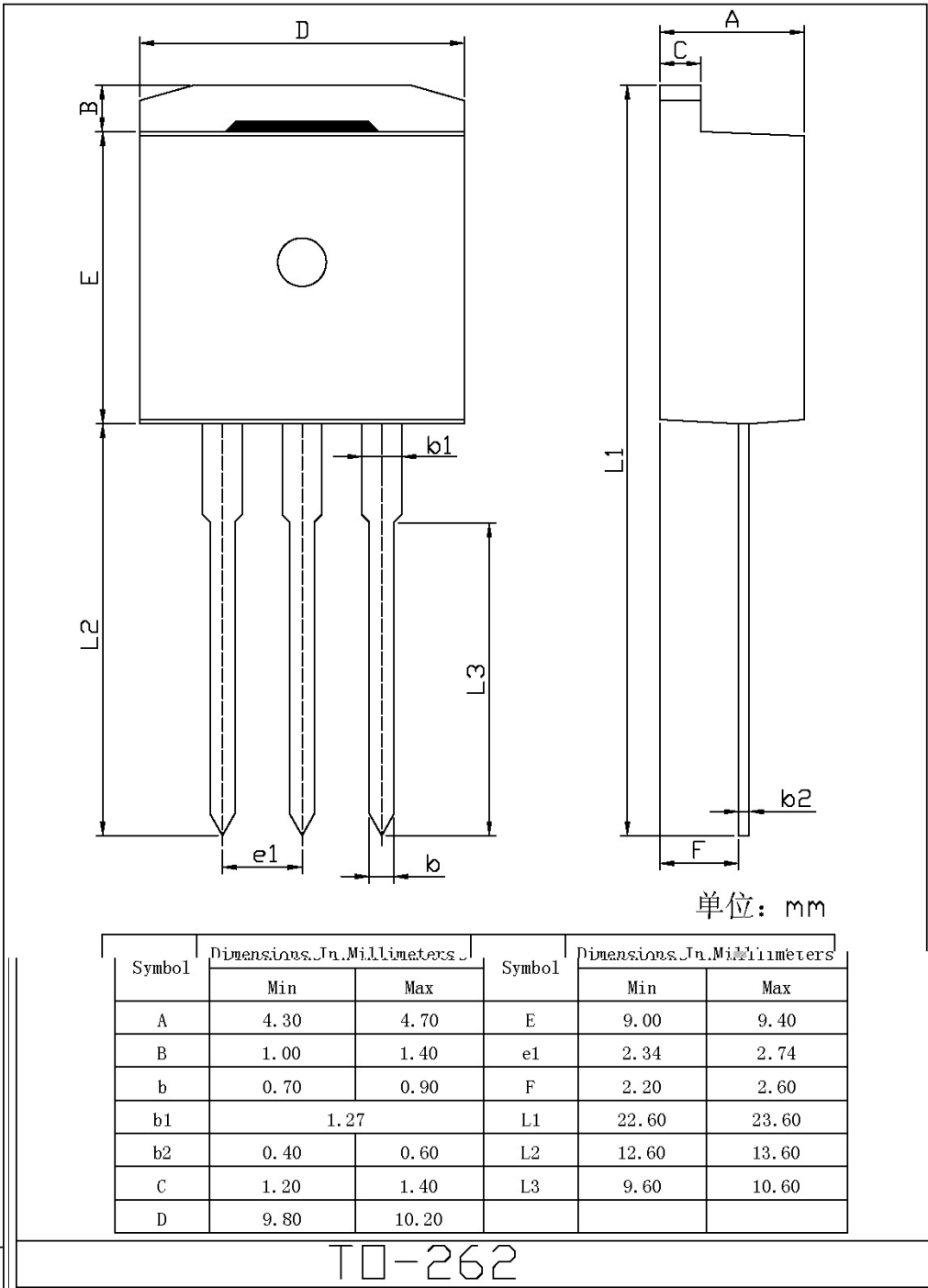
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	4.0	A
Drain Current	$I_D(T_C=100^\circ\text{C})$	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	240	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.0	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	100	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	600			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V$ $V_{GS}=0V$			10	μA
		$V_{DS}=480V$ $T_C=125^\circ\text{C}$			100	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 0.1	μA

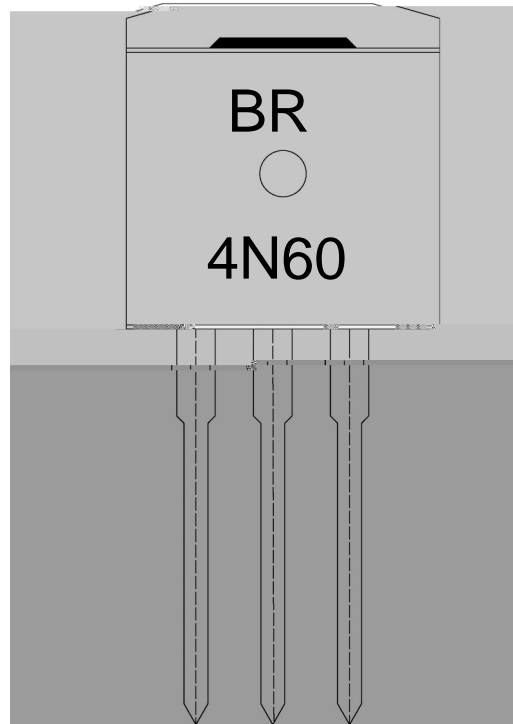
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR
4N60

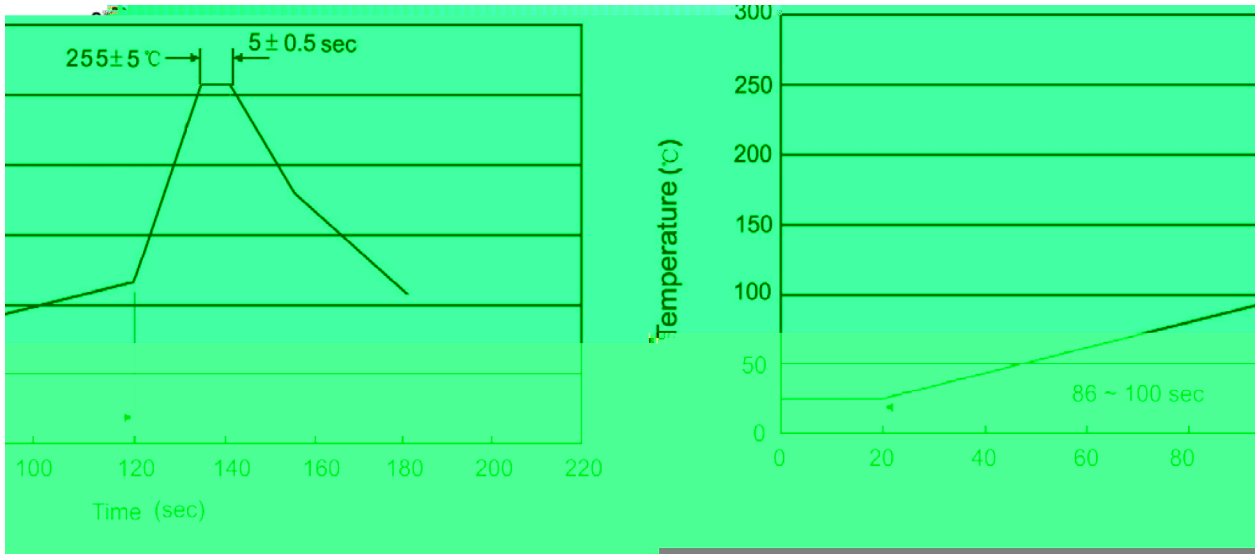
Note:

BR: Company Code

4N60: Product Type.

***: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1 25 150 60 90sec;
- 2 255 5 5 0.5sec;
- 3 2 10 /sec.

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255 5 , Duration:5 0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱